

AMENDMENTS TO THE SPECIFICATION

Please amend the paragraph bridging pages 2 and 3 as follows:

In the conventional photoelectric conversion device, a metal electrode layer 102 of Ag having a thickness of about 300 nm is formed on the upper surface of a glass substrate 101, as shown in Fig. 6. A transparent electrode 103 of aluminum-doped zinc oxide (AZO) having a thickness of about 100 nm is formed on the upper surface of the metal electrode layer 102. A power generation unit obtained by successively stacking an n layer 104 (thickness: about 50 nm) consisting of microcrystalline silicon (μ c-Si) doped with phosphorus, an i layer 105 (thickness: about 2 μ m) consisting of microcrystalline silicon (μ -Si) (μ c-Si) substantially doped with no impurity for deciding the conductivity type and a p layer 106 (thickness: about 10 nm) consisting of microcrystalline silicon (μ c-Si) doped with boron is formed on the upper surface of the transparent electrode 103. A transparent electrode 107 having a thickness of about 80 nm is formed on the power generation unit. A collector electrode 108 of silver paste are formed on prescribed portions of the upper surface of the transparent electrode 107. Thus constituted is the conventional photoelectric conversion device employing microcrystalline silicon (μ c-Si) as a photoelectric conversion layer (the power generation unit).

Please amend the paragraph bridging pages 16 and 17 as follows:

In the photoelectric conversion device according to the first embodiment, a metal electrode layer 2 of Ag having a thickness of about 300 nm is formed on the upper surface of a glass substrate 1, as shown in Fig. 1. A transparent electrode 3 of AZO (aluminum-doped zinc oxide) having a thickness of about 100 nm is formed on the upper surface of the metal electrode layer 2. The transparent electrode 3 is an example of the “electrode layer” in the present

invention. A power generation unit obtained by successively stacking an n layer 4 (thickness: about 50 nm) consisting of microcrystalline silicon ($\mu\text{-Si}$) ($\mu\text{c-Si}$) doped with phosphorus, an i layer 5 (thickness: about 2 Mm) consisting of microcrystalline silicon ($\mu\text{-Si}$) ($\mu\text{c-Si}$) substantially doped with no impurity for deciding the conductivity type and a p layer 6 (thickness: about 10 nm) consisting of microcrystalline silicon (pc-Si) doped with boron is formed on the upper surface of the transparent electrode 3. The n layer 4 and the p layer 6 are examples of the “first non-single-crystalline semiconductor layer” and the “second non-single-crystalline semiconductor layer” in the present invention respectively. The i layer 5 is an example of the “third non-single-crystalline semiconductor layer” in the present invention. Another transparent electrode 7 having a thickness of about 80 nm is formed on the upper surface of the power generation unit. Collectors 8 of silver paste are formed on prescribed portions of the upper surface of the transparent electrode 7. Thus constituted is the photoelectric conversion device according to the first embodiment, employing microcrystalline silicon ($\mu\text{-Si}$) ($\mu\text{c-Si}$) as a photoelectric conversion layer (the power generation unit).